

Kaoru Toko

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

245
papers

4,042
citations

32
h-index

49
g-index

273
ext. papers

4,725
ext. citations

2.5
avg, IF

5.7
L-index

#	Paper	IF	Citations
245	Growth conditions for high-photoresponsivity randomly oriented polycrystalline BaSi ₂ films by radio-frequency sputtering: Comparison with BaSi ₂ epitaxial films. <i>Applied Physics Express</i> , 2022 , 15, 025302	3.4	2
244	Three-Dimensionally Orientation-Controlled Ge Rods on an Insulator Formed by Low-Temperature Ni-Induced Lateral Crystallization. <i>Crystal Growth and Design</i> , 2022 , 22, 1123-1129	3.5	
243	High-temperature post-annealing effect on the surface morphology and photoresponse and electrical properties of B-doped BaSi ₂ films grown by molecular beam epitaxy under various Ba-to-Si deposition rate ratios. <i>Journal of Crystal Growth</i> , 2022 , 578, 126429	1.6	1
242	ZnGeO Passivating Interlayers for BaSi Thin-Film Solar Cells.. <i>ACS Applied Materials & Interfaces</i> , 2022 ,	9.5	1
241	Record-High Hole Mobility Germanium on Flexible Plastic with Controlled Interfacial Reaction. <i>ACS Applied Electronic Materials</i> , 2022 , 4, 269-275	4	1
240	High electron mobility in randomly oriented polycrystalline BaSi ₂ films formed through radio-frequency sputtering. <i>AIP Advances</i> , 2022 , 12, 045120	1.5	1
239	Sn Concentration Effects on Polycrystalline GeSn Thin Film Transistors. <i>IEEE Electron Device Letters</i> , 2021 , 42, 1735-1738	4.4	0
238	Effects of Ba-to-Si deposition rate ratios on the electrical and photoresponse properties of arsenic-doped n-type BaSi ₂ films. <i>Thin Solid Films</i> , 2021 , 738, 138969	2.2	0
237	Strain effects on polycrystalline germanium thin films. <i>Scientific Reports</i> , 2021 , 11, 8333	4.9	8
236	Comparison of C doping technique between SiC and C targets for high-photoresponsivity BaSi ₂ films by radio-frequency sputtering. <i>Japanese Journal of Applied Physics</i> , 2021 , 60, 058001	1.4	4
235	Mechanisms of carrier lifetime enhancement and conductivity-type switching on hydrogen-incorporated arsenic-doped BaSi ₂ . <i>Thin Solid Films</i> , 2021 , 724, 138629	2.2	5
234	Solar cell operation of sputter-deposited n-BaSi ₂ /p-Si heterojunction diodes and characterization of defects by deep-level transient spectroscopy. <i>Applied Physics Express</i> , 2021 , 14, 051010	2.4	2
233	Grain size dependent photoresponsivity in GaAs films formed on glass with Ge seed layers. <i>Scientific Reports</i> , 2021 , 11, 10159	4.9	1
232	Solid-phase crystallization of gallium arsenide thin films on insulators. <i>Materials Science in Semiconductor Processing</i> , 2021 , 124, 105623	4.3	1
231	Formation of high-photoresponsivity BaSi ₂ films on glass substrate by radio-frequency sputtering for solar cell applications. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 135106	3	6
230	Thickness-dependent thermoelectric properties of Si _{1-x} Gex films formed by Al-induced layer exchange. <i>Journal of Applied Physics</i> , 2021 , 129, 015303	2.5	4
229	High thermoelectric power factors in polycrystalline germanium thin films. <i>Applied Physics Letters</i> , 2021 , 119, 132101	3.4	1

228	Layer exchange synthesis of multilayer graphene. <i>Nanotechnology</i> , 2021 , 32,	3.4	3
227	Composition dependent properties of p- and n-type polycrystalline group-IV alloy thin films. <i>Journal of Alloys and Compounds</i> , 2021 , 887, 161306	5.7	3
226	Effect of post-annealing on the significant photoresponsivity enhancement of BaSi ₂ epitaxial films on Si(111). <i>Applied Physics Express</i> , 2021 , 14, 021003	2.4	2
225	Zn-induced layer exchange of p- and n-type nanocrystalline SiGe layers for flexible thermoelectrics. <i>Applied Physics Letters</i> , 2020 , 116, 182105	3.4	8
224	Metal-induced layer exchange of group IV materials. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 3730023		22
223	Drastic enhancement of photoresponsivity in C-doped BaSi ₂ films formed by radio-frequency sputtering. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SFFA06	1.4	4
222	Effects of sputtering pressure and temperature of ITO electrodes on the performance of p-BaSi ₂ /n-Si heterojunction solar cells. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SFFA07	1.4	
221	Significant enhancement of photoresponsivity in As-doped n-BaSi ₂ epitaxial films by atomic hydrogen passivation. <i>Applied Physics Express</i> , 2020 , 13, 051001	2.4	5
220	Effects of boron and hydrogen doping on the enhancement of photoresponsivity and photoluminescence of BaSi ₂ epitaxial films. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SFFA08	1.4	2
219	Fabrication of As-doped n-type BaSi ₂ epitaxial films grown by molecular beam epitaxy. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SFFA01	1.4	6
218	Atomic hydrogen passivation for photoresponsivity enhancement of boron-doped p-BaSi ₂ films and performance improvement of boron-doped p-BaSi ₂ /n-Si heterojunction solar cells. <i>Journal of Applied Physics</i> , 2020 , 127, 233104	2.5	8
217	Strong correlation between uniaxial magnetic anisotropic constant and in-plane tensile strain in Mn ₄ N epitaxial films. <i>AIP Advances</i> , 2020 , 10, 025117	1.5	15
216	Manipulation of saturation magnetization and perpendicular magnetic anisotropy in epitaxial CoxMn ₄ N films with ferrimagnetic compensation. <i>Physical Review B</i> , 2020 , 101,	3.3	11
215	Perpendicular magnetic anisotropy in ferrimagnetic Mn ₄ N films grown on (LaAlO ₃) _{0.3} (Sr ₂ TaAlO ₆) _{0.7} (001) substrates by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2020 , 535, 125566	1.6	9
214	Improving photoresponsivity in GaAs film grown on Al-induced-crystallized Ge on an insulator. <i>AIP Advances</i> , 2020 , 10, 015153	1.5	3
213	Fabrication of high-photoresponsivity BaSi ₂ films formed on conductive layers by radio-frequency sputtering. <i>Applied Physics Express</i> , 2020 , 13, 075506	2.4	1
212	Improved thermoelectric performance of flexible p-type SiGe films by B-doped Al-induced layer exchange. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 075105	3	6
211	Magnetic reversal in rare-earth free Mn ₄ kNixN epitaxial films below and above Ni composition needed for magnetic compensation around room temperature. <i>Journal of Applied Physics</i> , 2020 , 127, 043903	2.5	14

210	Impact of the carbon membrane inserted below Ni in the layer exchange of multilayer graphene. <i>CrystEngComm</i> , 2020 , 22, 3106-3109	3.3	1
209	Effects of molecular beam epitaxy growth conditions on grain size and lattice strain in a-axis-oriented BaSi ₂ films. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SFFA09	1.4	3
208	Impact of radio-frequency power on the photoresponsivity enhancement of BaSi ₂ films formed by sputtering. <i>Applied Physics Express</i> , 2020 , 13, 085511	2.4	6
207	Four-step heating process for solid-phase crystallization of Ge leading to high carrier mobility. <i>Applied Physics Express</i> , 2020 , 13, 101005	2.4	2
206	Magnetic compensation at two different composition ratios in rare-earth-free Mn ₄ Co _x N ferrimagnetic films. <i>Physical Review Materials</i> , 2020 , 4,	3.2	11
205	Modeling the effects of defect parameters on the performance of a p-BaSi ₂ /n-Si heterojunction solar cell. <i>Solar Energy Materials and Solar Cells</i> , 2020 , 205, 110244	6.4	3
204	Influence of Ba-to-Si deposition rate ratios on the electrical and optical properties of B-doped BaSi ₂ epitaxial films. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, SFFA04	1.4	6
203	Fe-induced layer exchange of multilayer graphene for rechargeable battery anodes. <i>Applied Physics Express</i> , 2020 , 13, 025501	2.4	4
202	Thin-film thermoelectric generator based on polycrystalline SiGe formed by Ag-induced layer exchange. <i>Applied Physics Letters</i> , 2020 , 117, 162103	3.4	3
201	Multilayer Graphene Battery Anodes on Plastic Sheets for Flexible Electronics. <i>ACS Applied Energy Materials</i> , 2020 , 3, 8410-8414	6.1	2
200	Influence of grain boundaries on the properties of polycrystalline germanium. <i>Journal of Applied Physics</i> , 2020 , 128, 075301	2.5	2
199	350 °C synthesis of high-quality multilayer graphene on an insulator using Ni-induced layer exchange. <i>Applied Physics Express</i> , 2020 , 13, 055502	2.4	6
198	Impact of deposition pressure and two-step growth technique on the photoresponsivity enhancement of polycrystalline BaSi ₂ films formed by sputtering. <i>Applied Physics Express</i> , 2019 , 12, 021004	2.4	9
197	Magnetic and magneto-transport properties of Mn ₄ N thin films by Ni substitution and their possibility of magnetic compensation. <i>Journal of Applied Physics</i> , 2019 , 125, 213902	2.5	19
196	Investigation of native defects in BaSi ₂ epitaxial films by electron paramagnetic resonance. <i>Applied Physics Express</i> , 2019 , 12, 061005	2.4	7
195	80 °C synthesis of thermoelectric nanocrystalline Ge film on flexible plastic substrate by Zn-induced layer exchange. <i>Applied Physics Express</i> , 2019 , 12, 055501	2.4	9
194	Minority carrier lifetime of Ge film epitaxial grown on a large-grain seed layer on glass. <i>Thin Solid Films</i> , 2019 , 681, 98-102	2.2	2
193	Solid-phase crystallization of densified amorphous GeSn leading to high hole mobility (540 cm ² /Vs). <i>Applied Physics Letters</i> , 2019 , 114, 112110	3.4	10

192	Operation of BaSi ₂ homojunction solar cells on p+-Si(111) substrates and the effect of structure parameters on their performance. <i>Applied Physics Express</i> , 2019 , 12, 041005	2.4	32
191	High-Electrical-Conductivity Multilayer Graphene Formed by Layer Exchange with Controlled Thickness and Interlayer. <i>Scientific Reports</i> , 2019 , 9, 4068	4.9	48
190	High photoresponsivity in a GaAs film synthesized on glass using a pseudo-single-crystal Ge seed layer. <i>Applied Physics Letters</i> , 2019 , 114, 142103	3.4	7
189	Low-Temperature (400 °C) Synthesis of Multilayer Graphene by Metal-Assisted Sputtering Deposition. <i>ACS Omega</i> , 2019 , 4, 6677-6680	3.9	12
188	Sb-doped crystallization of densified precursor for n-type polycrystalline Ge on an insulator with high carrier mobility. <i>Applied Physics Letters</i> , 2019 , 114, 082105	3.4	14
187	Simple way of finding Ba to Si deposition rate ratios for high photoresponsivity in BaSi ₂ films by Raman spectroscopy. <i>Applied Physics Express</i> , 2019 , 12, 055506	2.4	24
186	Impact of Amorphous-C/Ni Multilayers on Ni-Induced Layer Exchange for Multilayer Graphene on Insulators. <i>ACS Omega</i> , 2019 , 4, 14251-14254	3.9	4
185	Investigation of defect levels in BaSi ₂ epitaxial films by photoluminescence and the effect of atomic hydrogen passivation. <i>Journal of Physics Communications</i> , 2019 , 3, 075005	1.2	6
184	Polycrystalline thin-film transistors fabricated on high-mobility solid-phase-crystallized Ge on glass. <i>Applied Physics Letters</i> , 2019 , 114, 212107	3.4	17
183	Correlation of native defects between epitaxial films and polycrystalline BaSi ₂ bulks based on photoluminescence spectra. <i>Applied Physics Express</i> , 2019 , 12, 111001	2.4	3
182	Marked enhancement of the photoresponsivity and minority-carrier lifetime of BaSi ₂ passivated with atomic hydrogen. <i>Physical Review Materials</i> , 2019 , 3,	3.2	15
181	High-electron-mobility (370 cm ² /Vs) polycrystalline Ge on an insulator formed by As-doped solid-phase crystallization. <i>Scientific Reports</i> , 2019 , 9, 16558	4.9	12
180	Three-step growth of highly photoresponsive BaSi ₂ light absorbing layers with uniform Ba to Si atomic ratios. <i>Journal of Applied Physics</i> , 2019 , 126, 215301	2.5	13
179	High hole mobility (500 cm ² V ⁻¹ s ⁻¹) polycrystalline Ge films on GeO ₂ -coated glass and plastic substrates. <i>Applied Physics Express</i> , 2019 , 12, 015508	2.4	20
178	Molecular beam epitaxy growth of Mn _{4-x} Ni _x N thin films on MgO(0 0 1) substrates and their magnetic properties. <i>Journal of Crystal Growth</i> , 2019 , 507, 163-167	1.6	15
177	Epitaxial growth and magnetic properties of Fe _{4-x} Mn _x N thin films grown on MgO(0 0 1) substrates by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2018 , 489, 20-23	1.6	16
176	Impact of Ba to Si deposition rate ratios during molecular beam epitaxy on carrier concentration and spectral response of BaSi ₂ epitaxial films. <i>Journal of Applied Physics</i> , 2018 , 123, 045703	2.5	41
175	Advanced solid-phase crystallization for high-hole mobility (450 cm ² V ⁻¹ s ⁻¹) Ge thin film on insulator. <i>Applied Physics Express</i> , 2018 , 11, 031302	2.4	18

174	Reduction in interface defect density in p-BaSi ₂ /n-Si heterojunction solar cells by a modified pretreatment of the Si substrate. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 025501	1.4	6
173	Structural characterization and magnetic properties of L10-MnAl films grown on different underlayers by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2018 , 486, 19-23	1.6	3
172	Decrease in electrical contact resistance of Sb-doped n+-BaSi ₂ layers and spectral response of an Sb-doped n+-BaSi ₂ /undoped BaSi ₂ structure for solar cells. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 031202	1.4	2
171	p-BaSi ₂ /n-Si heterojunction solar cells on Si(001) with conversion efficiency approaching 10%: comparison with Si(111). <i>Applied Physics Express</i> , 2018 , 11, 062301	2.4	25
170	Detection of local vibrational modes induced by intrinsic defects in undoped BaSi ₂ light absorber layers using Raman spectroscopy. <i>Journal of Applied Physics</i> , 2018 , 124, 025301	2.5	16
169	Fabrication of SrGe thin films on Ge (100), (110), and (111) substrates. <i>Nanoscale Research Letters</i> , 2018 , 13, 22	5	1
168	Investigation of electrically active defects in undoped BaSi ₂ light absorber layers using deep-level transient spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 075801	1.4	8
167	Spectroscopic evidence of photogenerated carrier separation by built-in electric field in Sb-doped n-BaSi ₂ /B-doped p-BaSi ₂ homojunction diodes. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 050310	1.4	14
166	Millimeter-sized magnetic domains in perpendicularly magnetized ferrimagnetic Mn ₄ N thin films grown on SrTiO ₃ . <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 120310	1.4	16
165	Metal Catalysts for Layer-Exchange Growth of Multilayer Graphene. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 41664-41669	9.5	16
164	Significant photoresponsivity enhancement of polycrystalline BaSi ₂ films formed on heated Si(111) substrates by sputtering. <i>Applied Physics Express</i> , 2018 , 11, 071401	2.4	15
163	Improving carrier mobility of polycrystalline Ge by Sn doping. <i>Scientific Reports</i> , 2018 , 8, 14832	4.9	28
162	Improving the photoresponse spectra of BaSi ₂ layers by capping with hydrogenated amorphous Si layers prepared by radio-frequency hydrogen plasma. <i>AIP Advances</i> , 2018 , 8, 055306	1.5	7
161	Effect of BaSi ₂ template growth duration on the generation of defects and performance of p-BaSi ₂ /n-Si heterojunction solar cells. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 042301	1.4	4
160	Thermoelectric Inorganic SiGe Film Synthesized on Flexible Plastic Substrate. <i>ACS Applied Energy Materials</i> , 2018 ,	6.1	17
159	High-hole mobility Si _{1-x} Ge _x (0.1 ≤ x ≤ 1) on an insulator formed by advanced solid-phase crystallization. <i>Journal of Alloys and Compounds</i> , 2018 , 766, 417-420	5.7	9
158	Direct synthesis of multilayer graphene on an insulator by Ni-induced layer exchange growth of amorphous carbon. <i>Applied Physics Letters</i> , 2017 , 110, 033108	3.4	24
157	Highly oriented epitaxial (Fe ₂₊) ₁₆ N ₂ films on Fe(001) buffered MgAl ₂ O ₄ (001) substrates and their magnetization. <i>Journal of Crystal Growth</i> , 2017 , 468, 691-695	1.6	3

156	Effects of Al grain size on metal-induced layer exchange growth of amorphous Ge thin film on glass substrate. <i>Thin Solid Films</i> , 2017 , 626, 190-193	2.2	5
155	Control of grain size and crystallinity of poly-Si films on quartz by Al-induced crystallization. <i>CrystEngComm</i> , 2017 , 19, 2305-2311	3.3	19
154	Fabrication and characterizations of nitrogen-doped BaSi ₂ epitaxial films grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2017 , 471, 37-41	1.6	
153	Effect of p-BaSi ₂ layer thickness on the solar cell performance of p-BaSi ₂ /n-Si heterojunction solar cells. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 05DB03	1.4	14
152	Boron-doped p-BaSi ₂ /n-Si solar cells formed on textured n-Si(0 0 1) with a pyramid structure consisting of {1 1 1} facets. <i>Journal of Crystal Growth</i> , 2017 , 475, 186-191	1.6	6
151	Enhanced spectral response of semiconducting BaSi ₂ films by oxygen incorporation. <i>Thin Solid Films</i> , 2017 , 629, 17-21	2.2	10
150	Growth of BaSi ₂ continuous films on Ge(111) by molecular beam epitaxy and fabrication of p-BaSi ₂ /n-Ge heterojunction solar cells. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 05DB02	1.4	7
149	Minority-carrier lifetime and photoresponse properties of B-doped p-BaSi ₂ , a potential light absorber for solar cells. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 05DB01	1.4	5
148	Low temperature synthesis of highly oriented p-type Si _{1-x} Ge _x (x: 0.1) on an insulator by Al-induced layer exchange. <i>Journal of Applied Physics</i> , 2017 , 122, 155305	2.5	17
147	High-quality multilayer graphene on an insulator formed by diffusion controlled Ni-induced layer exchange. <i>Applied Physics Letters</i> , 2017 , 111, 243104	3.4	20
146	Multilayer graphene on insulator formed by Co-induced layer exchange. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 05DE03	1.4	8
145	Effect of interlayer on silver-induced layer exchange crystallization of amorphous germanium thin film on insulator. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 05DE04	1.4	4
144	High-hole mobility polycrystalline Ge on an insulator formed by controlling precursor atomic density for solid-phase crystallization. <i>Scientific Reports</i> , 2017 , 7, 16981	4.9	51
143	Silver-induced layer exchange for polycrystalline germanium on a flexible plastic substrate. <i>Journal of Applied Physics</i> , 2017 , 122, 215305	2.5	12
142	Perpendicular magnetic anisotropy in Co _x Mn _{4-x} N (x = 0 and 0.2) epitaxial films and possibility of tetragonal Mn ₄ N phase. <i>AIP Advances</i> , 2016 , 6, 056201	1.5	25
141	Orientation control of intermediate-composition SiGe on insulator by low-temperature Al-induced crystallization. <i>Scripta Materialia</i> , 2016 , 122, 86-88	5.6	14
140	Control of electrical properties of BaSi ₂ thin films by alkali-metal doping using alkali-metal fluorides. <i>Thin Solid Films</i> , 2016 , 603, 218-223	2.2	6
139	Evaluation of band offset at amorphous-Si/BaSi ₂ interfaces by hard x-ray photoelectron spectroscopy. <i>Journal of Applied Physics</i> , 2016 , 119, 165304	2.5	23

138	Effect of amorphous Si capping layer on the hole transport properties of BaSi ₂ and improved conversion efficiency approaching 10% in p-BaSi ₂ /n-Si solar cells. <i>Applied Physics Letters</i> , 2016 , 109, 072103	3.4	82
137	Measurement of valence-band offset at native oxide/BaSi ₂ interfaces by hard x-ray photoelectron spectroscopy. <i>Journal of Applied Physics</i> , 2016 , 119, 025306	2.5	17
136	Electrical detection of magnetic domain wall in Fe ₄ N nanostrip by negative anisotropic magnetoresistance effect. <i>Journal of Applied Physics</i> , 2016 , 120, 113903	2.5	1
135	p-BaSi ₂ /n-Si heterojunction solar cells with conversion efficiency reaching 9.0%. <i>Applied Physics Letters</i> , 2016 , 108, 152101	3.4	62
134	Influence of air exposure duration and a-Si capping layer thickness on the performance of p-BaSi ₂ /n-Si heterojunction solar cells. <i>AIP Advances</i> , 2016 , 6, 085107	1.5	34
133	Epitaxial growth and magnetic properties of NixFe _{4-x} N (x = 0, 1, 3, and 4) films on SrTiO ₃ (001) substrates. <i>Journal of Applied Physics</i> , 2016 , 120, 083907	2.5	12
132	Sn-inserted Al-induced layer exchange for large-grained GeSn thin films on insulator. <i>Thin Solid Films</i> , 2016 , 616, 316-319	2.2	1
131	Growth and magnetic properties of epitaxial Fe ₄ N films on insulators possessing lattice spacing close to Si(001) plane. <i>Journal of Crystal Growth</i> , 2016 , 455, 66-70	1.6	7
130	Fabrication of L-shaped Fe ₄ N ferromagnetic narrow wires and position control of magnetic domain wall with magnetic field. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 028003	1.4	3
129	Cross-sectional potential profile across a BaSi ₂ pn junction by Kelvin probe force microscopy. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 030306	1.4	3
128	Local electronic states of Fe ₄ N films revealed by x-ray absorption spectroscopy and x-ray magnetic circular dichroism. <i>Journal of Applied Physics</i> , 2015 , 117, 193906	2.5	16
127	Vertically Aligned Ge Nanowires on Flexible Plastic Films Synthesized by (111)-Oriented Ge Seeded Vapor-Liquid-Solid Growth. <i>ACS Applied Materials & Interfaces</i> , 2015 , 7, 18120-4	9.5	19
126	Effects of flexible substrate thickness on Al-induced crystallization of amorphous Ge thin films. <i>Thin Solid Films</i> , 2015 , 583, 221-225	2.2	8
125	70 °C synthesis of high-Sn content (25%) GeSn on insulator by Sn-induced crystallization of amorphous Ge. <i>Applied Physics Letters</i> , 2015 , 106, 082109	3.4	55
124	Mössbauer study on epitaxial CoFe ₄ N films grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2015 , 117, 17B717	2.5	5
123	Effect of Diffusion Control Layer on Reverse Al-Induced Layer Exchange Process for High-Quality Ge/Al/Glass Structure. <i>Journal of Electronic Materials</i> , 2015 , 44, 1377-1381	1.9	1
122	Formation of BaSi ₂ heterojunction solar cells using transparent MoO _x hole transport layers. <i>Applied Physics Letters</i> , 2015 , 106, 122104	3.4	15
121	Characterization of defect levels in undoped n-BaSi ₂ epitaxial films on Si(111) by deep-level transient spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 07JE01	1.4	9

120	Transfer-free synthesis of highly ordered Ge nanowire arrays on glass substrates. <i>Applied Physics Letters</i> , 2015 , 107, 133102	3.4	6
119	Influence of Substrate on Crystal Orientation of Large-Grained Si Thin Films Formed by Metal-Induced Crystallization. <i>International Journal of Photoenergy</i> , 2015 , 2015, 1-7	2.1	10
118	2015 ,		1
117	Improved Surface Quality of the Metal-Induced Crystallized Ge Seed Layer and Its Influence on Subsequent Epitaxy. <i>Crystal Growth and Design</i> , 2015 , 15, 1535-1539	3.5	26
116	Potential variations around grain boundaries in impurity-doped BaSi ₂ epitaxial films evaluated by Kelvin probe force microscopy. <i>Journal of Applied Physics</i> , 2014 , 116, 123709	2.5	20
115	Diffusion coefficients of impurity atoms in BaSi ₂ epitaxial films grown by molecular beam epitaxy. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 04ER02	1.4	7
114	Influence of grain size and surface condition on minority-carrier lifetime in undoped n-BaSi ₂ on Si(111). <i>Journal of Applied Physics</i> , 2014 , 115, 193510	2.5	64
113	N-type doping of BaSi ₂ epitaxial films by arsenic ion implantation through a dose-dependent carrier generation mechanism. <i>Thin Solid Films</i> , 2014 , 567, 105-108	2.2	20
112	Direct synthesis of highly textured Ge on flexible polyimide films by metal-induced crystallization. <i>Applied Physics Letters</i> , 2014 , 104, 262107	3.4	17
111	Orientation control of Ge thin films by underlayer-selected Al-induced crystallization. <i>CrystEngComm</i> , 2014 , 16, 2578	3.3	17
110	Self-organization of Ge(111)/Al/glass structures through layer exchange in metal-induced crystallization. <i>CrystEngComm</i> , 2014 , 16, 9590-9595	3.3	8
109	Coherent lateral-growth of Ge over insulating film by rapid-melting-crystallization. <i>Thin Solid Films</i> , 2014 , 557, 135-138	2.2	1
108	Precipitation control and activation enhancement in boron-doped p+-BaSi ₂ films grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2014 , 104, 252104	3.4	27
107	Analysis of the electrical properties of Cr/n-BaSi ₂ Schottky junction and n-BaSi ₂ /p-Si heterojunction diodes for solar cell applications. <i>Journal of Applied Physics</i> , 2014 , 115, 223701	2.5	41
106	Evaluation of minority carrier diffusion length of undoped n-BaSi ₂ epitaxial thin films on Si(001) substrates by electron-beam-induced-current technique. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 078004	1.4	16
105	Growth promotion of Al-induced crystallized Ge films on insulators by insertion of a Ge membrane below the Al layer. <i>Thin Solid Films</i> , 2014 , 557, 143-146	2.2	12
104	Large-grained (111)-oriented Si/Al/SiO ₂ structures formed by diffusion-controlled Al-induced layer exchange. <i>Thin Solid Films</i> , 2014 , 557, 147-150	2.2	6
103	N-type doping of BaSi ₂ epitaxial films by phosphorus ion implantation and thermal annealing. <i>Thin Solid Films</i> , 2014 , 557, 90-93	2.2	23

102	Fabrication and characterization of BaSi ₂ epitaxial films over 1 μm in thickness on Si(111). <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 04ER04	1.4	29
101	Potential variation around grain boundaries in BaSi ₂ films grown on multicrystalline silicon evaluated using Kelvin probe force microscopy. <i>Journal of Applied Physics</i> , 2014 , 116, 235301	2.5	6
100	Low-temperature (180 °C) formation of large-grained Ge (111) thin film on insulator using accelerated metal-induced crystallization. <i>Applied Physics Letters</i> , 2014 , 104, 022106	3.4	88
99	Photoresponse properties of undoped BaSi ₂ epitaxial layers on n+-BaSi ₂ /p+-Si(001) by molecular beam epitaxy. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 058007	1.4	14
98	Selective formation of large-grained, (100)- or (111)-oriented Si on glass by Al-induced layer exchange. <i>Journal of Applied Physics</i> , 2014 , 115, 094301	2.5	36
97	Sign of the spin-polarization in cobalt-iron nitride films determined by the anisotropic magnetoresistance effect. <i>Journal of Applied Physics</i> , 2014 , 116, 053912	2.5	35
96	Perpendicular magnetic anisotropy of Mn ₄ N films on MgO(001) and SrTiO ₃ (001) substrates. <i>Journal of Applied Physics</i> , 2014 , 115, 17A935	2.5	57
95	Al-induced crystallization of amorphous Ge thin films on conducting layer coated glass substrates. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 04EH01	1.4	6
94	Structural characterization of polycrystalline Ge thin films on insulators formed by diffusion-enhanced Al-induced layer exchange. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 04EH03	1.4	7
93	X-ray magnetic circular dichroism for Co _x Fe _{4-x} N (x = 0, 3, 4) films grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2014 , 115, 17C712	2.5	18
92	Temperature dependent Al-induced crystallization of amorphous Ge thin films on SiO ₂ substrates. <i>Journal of Crystal Growth</i> , 2013 , 372, 189-192	1.6	13
91	Orientation Control of Large-Grained Si Films on Insulators by Thickness-Modulated Al-Induced Crystallization. <i>Crystal Growth and Design</i> , 2013 , 13, 1767-1770	3.5	43
90	Lattice and grain-boundary diffusions of boron atoms in BaSi ₂ epitaxial films on Si(111). <i>Journal of Applied Physics</i> , 2013 , 113, 053511	2.5	19
89	In-situ heavily p-type doping of over 10 ²⁰ cm ⁻³ in semiconducting BaSi ₂ thin films for solar cells applications. <i>Applied Physics Letters</i> , 2013 , 102, 112107	3.4	59
88	Effect of atomic-hydrogen irradiation on reduction of residual carrier concentration in p-Si ₃ Si ₂ films grown on Si substrates by atomic-hydrogen-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2013 , 378, 365-367	1.6	2
87	Evaluation of diffusion coefficients of n-type impurities in MBE-grown BaSi ₂ epitaxial layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 1762-1764		1
86	Molecular beam epitaxy of boron doped p-type BaSi ₂ epitaxial films on Si(111) substrates for thin-film solar cells. <i>Journal of Crystal Growth</i> , 2013 , 378, 201-204	1.6	13
85	Structural study on phosphorus doping of BaSi ₂ epitaxial films by ion implantation. <i>Thin Solid Films</i> , 2013 , 534, 470-473	2.2	15

84	Formation of polycrystalline BaSi ₂ films by radio-frequency magnetron sputtering for thin-film solar cell applications. <i>Thin Solid Films</i> , 2013 , 534, 116-119	2.2	26
83	Formation of large-grain-sized BaSi ₂ epitaxial layers grown on Si(111) by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2013 , 378, 193-197	1.6	5
82	Epitaxial growth of ferromagnetic Co _x Fe _{4-x} N thin films on SrTiO ₃ (001) and magnetic properties. <i>Journal of Crystal Growth</i> , 2013 , 378, 342-346	1.6	5
81	Low-temperature crystallization of amorphous silicon and amorphous germanium by soft X-ray irradiation. <i>Thin Solid Films</i> , 2013 , 534, 334-340	2.2	12
80	Lattice and grain-boundary diffusions of impurity atoms in BaSi ₂ epitaxial layers grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2013 , 378, 189-192	1.6	7
79	Large photoresponsivity in semiconducting BaSi ₂ epitaxial films grown on Si(001) substrates by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2013 , 378, 198-200	1.6	4
78	Double-Layered Ge Thin Films on Insulators Formed by an Al-Induced Layer-Exchange Process. <i>Crystal Growth and Design</i> , 2013 , 13, 3908-3912	3.5	16
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66	Fabrication of n+-BaSi ₂ /p+-Si tunnel junction on Si(001) surface for characterization of photoresponse properties of BaSi ₂ epitaxial films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 1773-1776		
65	Fabrication of BaSi ₂ films on (111)-oriented Si layers formed by inverted Al-induced crystallization method on glass structure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 1769-1772	1	
64	Epitaxial growth of BaSi ₂ films with large grains using vicinal Si(111) substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 1756-1758	1	
63	Fabrication and characterization of polycrystalline BaSi ₂ by RF sputtering. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 1759-1761	39	
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